LISTING OF THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. **(Currently Amended)** A substrate processing apparatus for spraying gas [[to]] onto a substrate completely cleaned with deionized water for drying said substrate, comprising:

a first gas discharge element coupled to a source of said gas for spraying said gas [[to]] onto the surface of said substrate which is wet with said deionized water; and

a second gas discharge element coupled to said source of said gas, and a control to cause further spraying of said gas [[to]] onto the same region as the region [[already]] previously sprayed with said gas by said first gas discharge element.

2. **(Original)** The substrate processing apparatus according to claim 1, wherein the flow rate of said gas sprayed from said second gas discharge element to said substrate is larger than the flow rate of said gas sprayed from said first gas discharge element to said substrate.

3. **(Withdrawn)** The substrate processing apparatus according to claim 2, further comprising a rotation element rotating said substrate substantially in a horizontal plane, wherein,

said first gas discharge element comprises:

a first nozzle discharging said gas, and

a first nozzle moving element moving said first nozzle substantially in a horizontal plane,

said second gas discharge element comprises:

a second nozzle discharging said gas, and

a second nozzle moving element moving said nozzle substantially in a horizontal plane, and

said first nozzle moving element and said second nozzle moving element move the respective ones of said first nozzle and said second nozzle so that arrival points of said gas

discharged from the respective ones of said first nozzle and said second nozzle draw loci directed from the rotation center of rotated said substrate toward the edge.

4. (Withdrawn) The substrate processing apparatus according to claim 3, wherein said gas is inert gas.

5. (Currently Amended) A substrate processing apparatus spraying gas to a substrate completely cleaned with deionized water for drying said substrate, comprising:

a first nozzle spraying said gas to the surface of said substrate wet with said deionized water;

a second nozzle spraying said gas to the surface of said substrate;

a nozzle arm fixedly provided with said first nozzle and said second nozzle; [[and]]

a moving element moving said nozzle arm in a plane substantially parallel to said substrate; and

a rotation element rotating said substrate substantially in a horizontal plane, wherein

said moving element moves said nozzle arm substantially in a horizontal plane so that arrival points of said gas discharged from the respective ones of said first nozzle and said second nozzle draw loci directed from the rotation center of the rotated substrate toward the edge, thereby spraying said gas from said second nozzle to the same region as the region on said substrate once having been sprayed with said gas by said first nozzle.

~~said moving element moves said nozzle arm to spray said gas from said second nozzle to the same region as the region on said substrate sprayed with said gas by said first nozzle.~~

6. (Original) The substrate processing apparatus according to claim 5, wherein the flow rate of said gas sprayed from said second nozzle to said substrate is larger than the flow rate of said gas sprayed from said first nozzle to said substrate.

7. (Canceled)

8. **(Currently Amended)** The substrate processing apparatus according to claim [[7]] 6, wherein

said gas is inert gas.

9. **(Withdrawn)** A substrate processing apparatus spraying gas to a substrate completely cleaned with deionized water for drying said substrate, comprising:

a nozzle spraying said gas to the surface of said substrate wet with said deionized water;

a nozzle arm fixedly provided with said nozzle; and

a moving element moving said nozzle arm in a plane substantially parallel to said substrate, wherein

said moving element moves said nozzle arm to re-spray said gas by said nozzle to the same region as the region on said substrate sprayed with gas by said nozzle.

10. **(Withdrawn)** The substrate processing apparatus according to claim 9, wherein

the flow rate of said gas re-sprayed from said nozzle to said substrate is larger than the flow rate of said gas precedently sprayed from said nozzle to said substrate.

11. **(Withdrawn)** The substrate processing apparatus according to claim 10, further comprising a rotation element rotating said substrate substantially in a horizontal plane, wherein

said moving element moves said nozzle arm substantially in a horizontal plane so that arrival points of said gas precedently and subsequently discharged from said nozzle draw loci directed from the rotation center of rotated said substrate toward the edge.

12. **(Withdrawn)** The substrate processing apparatus according to claim 11, wherein

said gas is inert gas.

13. **(Withdrawn)** A substrate processing method spraying gas to a substrate completely cleaned with deionized water for drying said substrate, comprising steps of:

a) spraying said gas to the surface of said substrate wet with said deionized water; and

b) further spraying said gas to the same region as the region on said substrate already sprayed with said gas in said step a).

14. (Withdrawn) The substrate processing method according to claim 13, wherein the flow rate of said gas sprayed to said substrate in said step b) is larger than the flow rate of said gas sprayed to said substrate in said step a).

15. (Withdrawn) The substrate processing method according to claim 14, wherein said gas is inert gas.